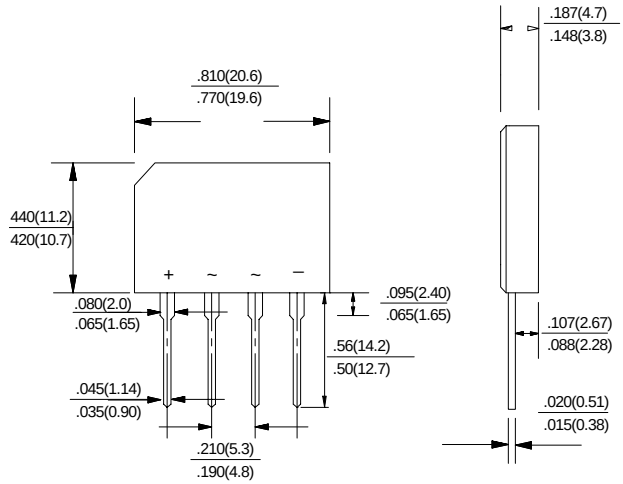
KBJ2A-KBJ2M

SILICON BRIDGE RECTIFIERS

VOLTAGE RANGE: 50 - 1000V
CURRENT: 2.0 A

KBJ2



Features

- Diffused Junction
- High Surge Current Capability
- High Current Capability
- High Reliability

Mechanical Data

- Case: Molded Plastic
- Terminals: Plated Leads Solderable per MIL-STD-202, Method 208
- Polarity: As Marked on Body
- Weight: 2.0 grams (approx.)
- Mounting Position: Any
- Marking: Type Number

RoHS COMPLIANT

Maximum Ratings and Electrical Characteristics T_A = 25°C unless otherwise specified

Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Characteristic	Symbol	KBJ2A	KBJ2B	KBJ2D	KBJ2G	KBJ2J	KBJ 2K	KBJ2M	Unit
Maximum recurrent peak reverse voltage	V_{RRM}	50	100	200	400	600	800	1000	V
Maximum RMS voltage	V_{RMS}	35	70	140	280	420	560	700	V
Maximum DC blocking voltage	V_{DC}	50	100	200	400	600	800	1000	V
Maximum average forw ard Output current @T_A=50 ℃	$I_{F(AV)}$	2.0							A
Peak forw ard surge current 8.3ms single half-sine-w ave superimposed on rated load	I_{FSM}	50.0							A
Maximum instantaneous forw ard voltage at 1.0 A	V_F	1.0							V
Maximum reverse current @T_A=25℃	I_R	10.0							μA
at rated DC blocking voltage @T_A=100℃		1.0							mA
Typical junction capacitance per element	C_J	45							pF
Typical thermal resistance	$R_{\theta JC}$	2.2							℃/W
Operating junction temperature range	T_J	- 55 ---- + 125							℃
Storage temperature range	T_{STG}	- 55 ---- + 150							℃

NOTES:1.Measured at 1.0MHz and applied reverse voltage of 4.0V DC

2.Device mounted on 300mm X 300mm X 1.6mm cu Plate heatsink.

FIG.1 -- PEAK FORWARD SURGE CURRENT

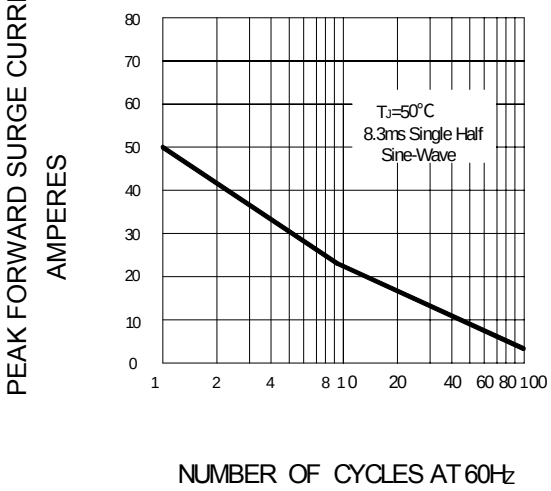


FIG.2 -- FORWARD DERATING CURVE

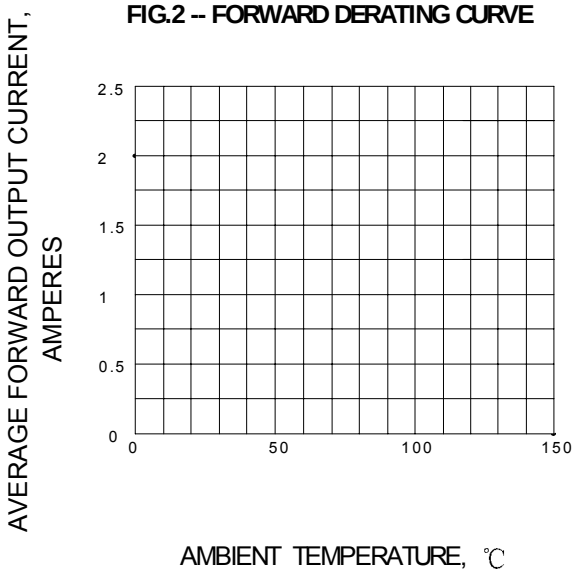


FIG.3 -- TYPICAL FORWARD CHARACTERISTIC

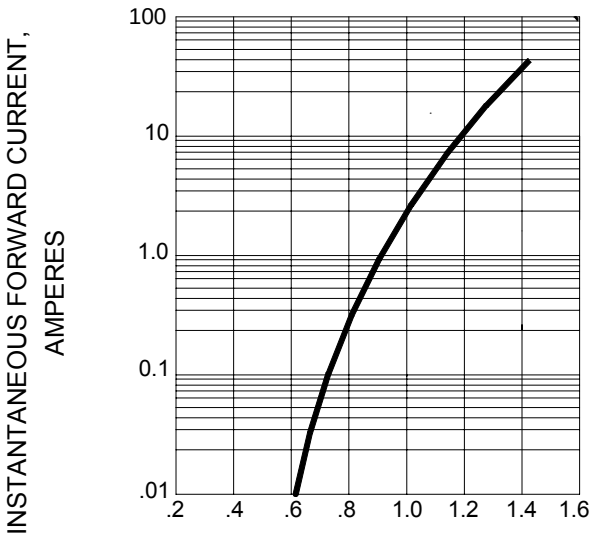


FIG.4 -- TYPICAL JUNCTION CAPACITANCE